Ordering number : ENA0434

SANYO Semiconductors
DATA SHEET

2SC6096 — NPN Epitaxial Planar Silicon Transistor
High-Voltage Switching Applications

Applications

- DC / DC converter, relay drivers, lamp drivers, motor drivers, inverter.

Features

- Adoption of FBET, MBIT process.
- High current capacitance.
- Low collector-to-emitter saturation voltage.
- High-speed switching.
- High allowable power dissipation.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		120	V
Collector-to-Emitter Voltage	V_{CES}		120	V
Collector-to-Emitter Voltage	V_{CEO}		100	V
Emitter-to-Base Voltage	V_{EBO}		6.5	V
Collector Current	I_C		2	A
Collector Current (Pulse)	I_{CP}		3	A
Base Current	I_B		400	mA
Collector Dissipation	P_C	Mounted on a ceramic board (250mm²×0.8mm)	1.3	W
		Tc=25°C	3.5	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	V_{CB}=80V, I_E=0A			1	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=4V, I_C=0A			1	μA
DC Current Gain	h_{FE}	V_{CE}=5V, I_C=100mA	300		600	

Marking : QG

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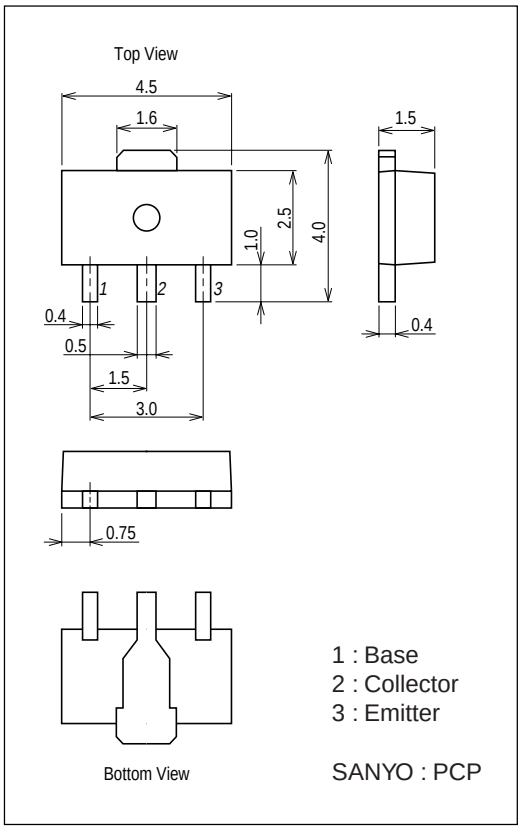
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Gain-Bandwidth Product	f_T	V_{CE}=10V, I_C=300mA		300		MHz
Output Capacitance	Cob	V_{CB}=10V, f=1MHz		13		pF
Collector-to-Emitter Saturation Voltage	V_{CE}(sat)	I_C=1A, I_B=100mA		100	150	mV
Base-to-Emitter Saturation Voltage	V_{BE}(sat)	I_C=1A, I_B=100mA		0.85	1.2	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=10μA, I_E=0A	120			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CES}$	I_C=100μA, R_{BE}=0Ω	120			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=1mA, R_{BE}=∞	100			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=10μA, I_C=0A	6.5			V
Turn-ON Time	t_{on}	See specified Test Circuit.		40		ns
Storage Time	t_{stg}	See specified Test Circuit.		1100		ns
Fall Time	t_f	See specified Test Circuit.		40		ns

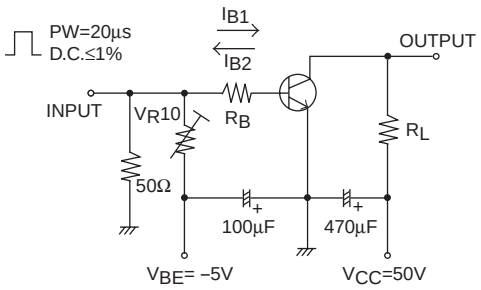
Package Dimensions

unit : mm

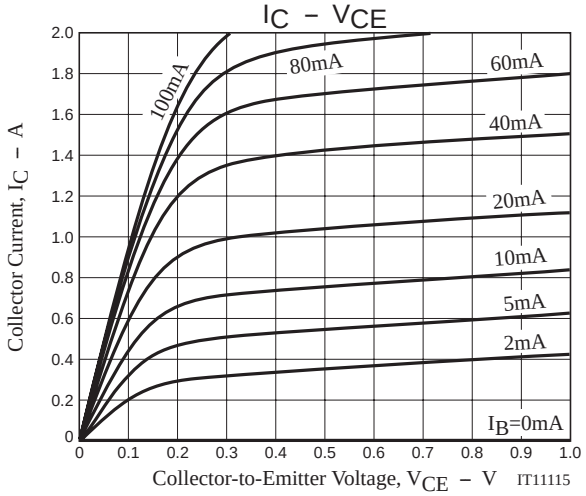
7007A-004

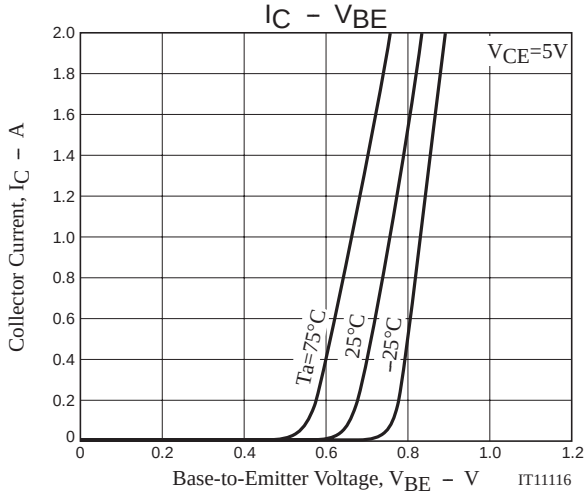


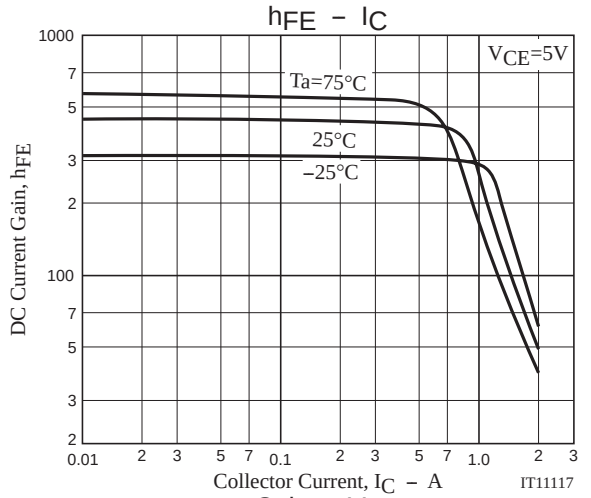
Switching Time Test Circuit

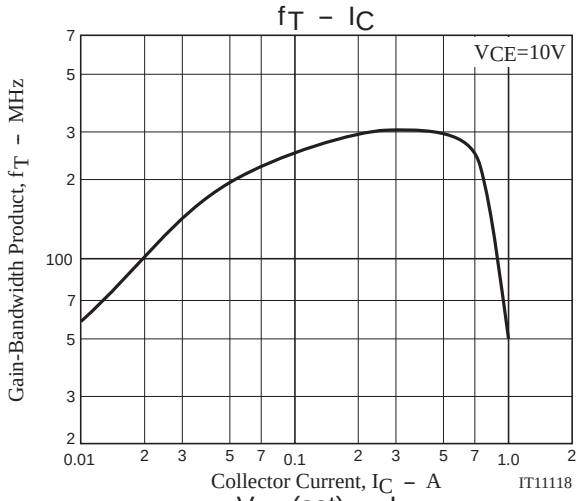


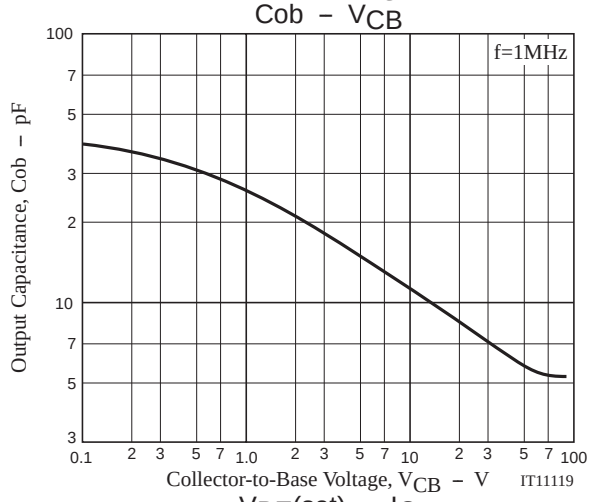
$10I_{B1}= -10I_{B2}=I_C=0.5A$

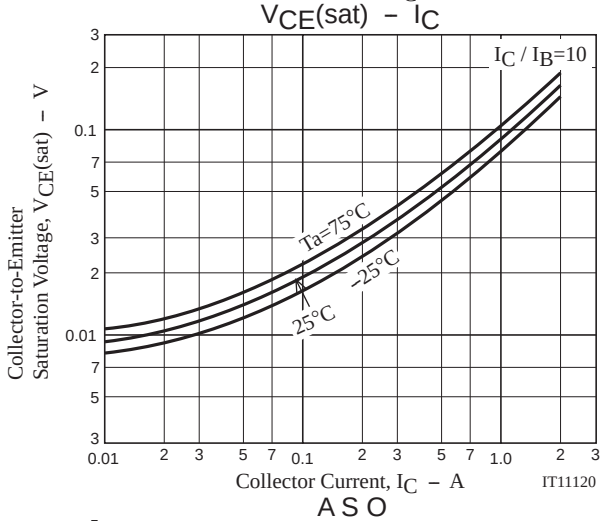


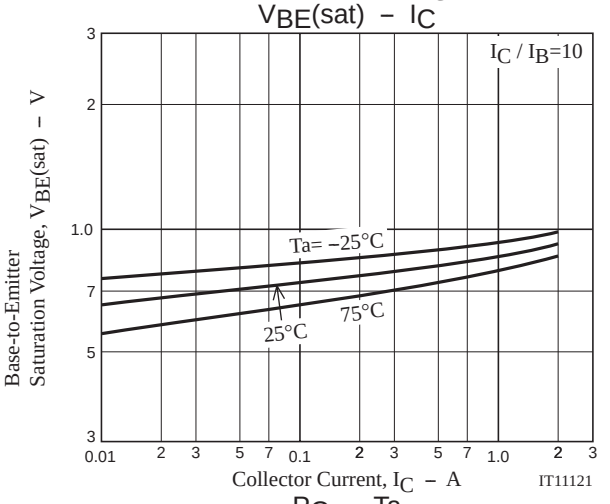


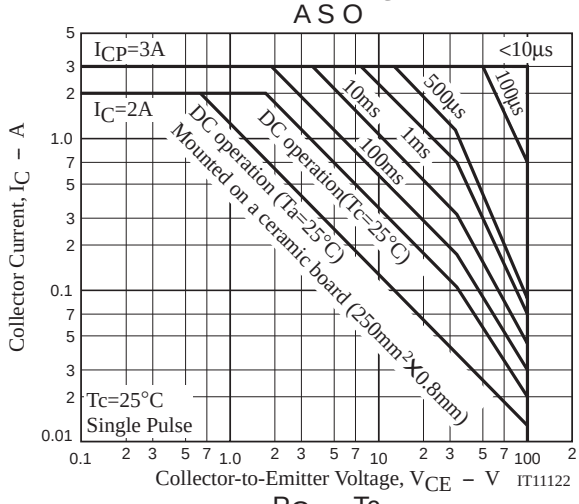

hFE – IC
VCE=5V
Ta=75°C
25°C
–25°C
DC Current Gain, hFE
Collector Current, IC – A
IT11117

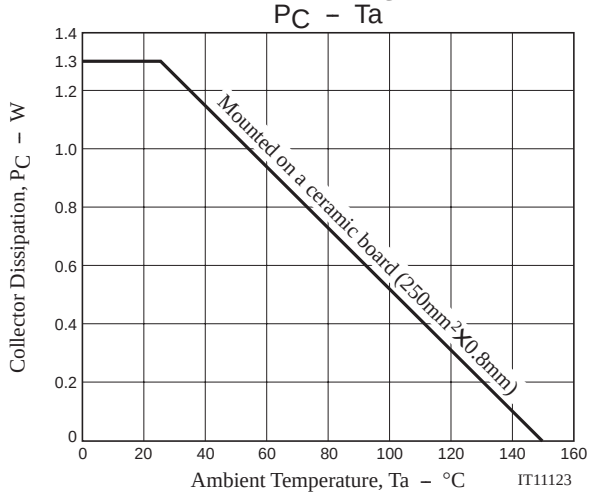

fT – IC
VCE=10V
Gain-Bandwidth Product, fT – MHz
Collector Current, IC – A
IT11118

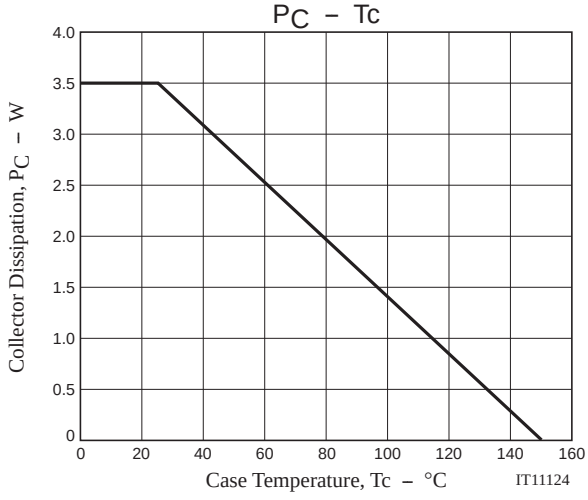

Cob – VCB
f=1MHz
Output Capacitance, Cob – pF
Collector-to-Base Voltage, VCB – V
IT11119


VCE(sat) – IC
IC / IB=10
Ta=75°C
–25°C
25°C
Collector-to-Emitter Saturation Voltage, VCE(sat) – V
Collector Current, IC – A
IT11120


VBE(sat) – IC
IC / IB=10
Ta= –25°C
75°C
25°C
Base-to-Emitter Saturation Voltage, VBE(sat) – V
Collector Current, IC – A
IT11121


ASO
ICP=3A
IC=2A
<10µs
500µs
100µs
10ms
1ms
100ms
DC operation (Ta=25°C)
DC operation(Tc=25°C)
Mounted on a ceramic board (250mm2×0.8mm)
Tc=25°C
Single Pulse
Collector Current, IC – A
Collector-to-Emitter Voltage, VCE – V
IT11122


PC – Ta
Mounted on a ceramic board (250mm2×0.8mm)
Collector Dissipation, PC – W
Ambient Temperature, Ta – °C
IT11123


PC – Tc
Collector Dissipation, PC – W
Case Temperature, Tc – °C
IT11124